

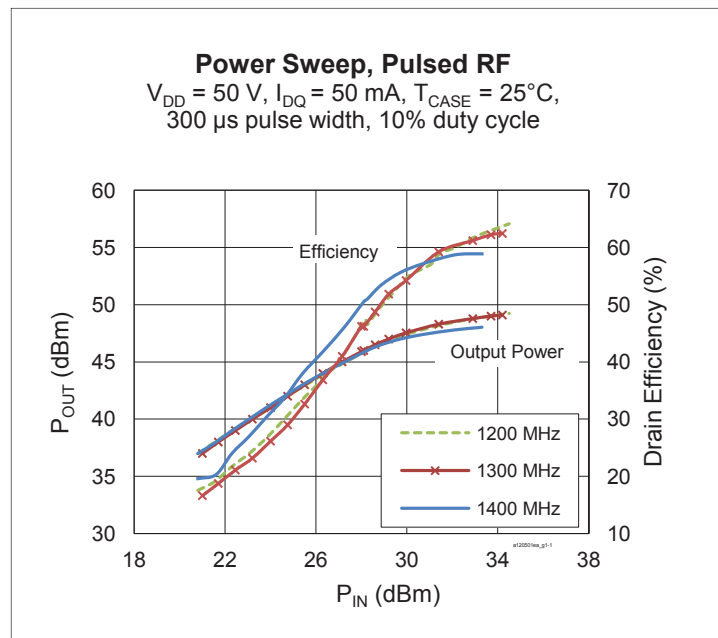
Thermally-Enhanced High Power RF LDMOS FET 50 W, 50 V, 1200 – 1400 MHz

Description

The PTVA120501EA LDMOS FET is designed for use in power amplifier applications in the 1200 to 1400 MHz frequency band. Features include high gain and thermally-enhanced package with bolt-down flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



PTVA120501EA
Package H-36265-2



Features

- Broadband input matching
- High gain and efficiency
- Typical Pulsed CW performance, 1200 – 1400MHz, 50 V, 300 μs pulse width, 10% duty cycle, class AB
 - Output power at $P_{1dB} = 54\text{ W}$
 - Efficiency = 55%
 - Gain = 16 dB
- Integrated ESD protection
- Low thermal resistance
- Pb-free and RoHS compliant
- Capable of withstanding a 10:1 load mismatch (all phase angles) at 50 W peak under RF pulse, 300 μs , 10% duty cycle.

RF Characteristics

Pulsed RF Performance (tested in Infineon test fixture)

$V_{DD} = 50\text{ V}$, $I_{DQ} = 50\text{ mA}$, $P_{OUT} = 50\text{ W}$, $f_1 = 1200\text{ MHz}$, $f_2 = 1300\text{ MHz}$, $f_3 = 1400\text{ MHz}$, 300 μs pulse width, 10% duty cycle

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	16.5	17	—	dB
Drain Efficiency	η_D	46	50	—	%
Return Loss	IRL	—	-10	-7	dB

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

RF Characteristics

Typical RF Performance (not subject to production test, verified by design/characterization in Infineon test fixture)

$V_{DD} = 50\text{ V}$, $I_{DQ} = 50\text{ mA}$, Input signal ($t_r = 7\text{ ns}$, $t_f = 8\text{ ns}$), $300\text{ }\mu\text{s}$ pulse width, 10% duty cycle, class AB test

Mode of Operation	f (MHz)	IRL (dB)	P _{1dB}			P _{3dB}			Max P _{droop} (pulse) dB @ 50 W	t_r (ns) @ 50 W*	t_f (ns) @ 50 W*
			Gain (dB)	Eff (%)	P _{OUT} (W)	Gain (dB)	Eff (%)	P _{OUT} (W)			
Pulsed RF	1200	-8	16	56	60	14	58	78	0.20	5	<2
Pulsed RF	1300	-10	16	57	60	14	58	78	0.20	5	<2
Pulsed RF	1400	-8	16	55	54	14	57	57	0.15	5	<2

* Note = t_r and t_f are defined as Δ between input and output rise and fall times

Typical RF Performance (not subject to production test, verified by design/characterization in Infineon test fixture)

$V_{DD} = 50\text{ V}$, $I_{DQ} = 50\text{ mA}$, 30 ms pulse width, 33% duty cycle, class AB test

Mode of Operation	f (MHz)	P _{1dB}			P _{3dB}			P _{droop} (pulse) dB @ 50 W
		Gain (dB)	Eff (%)	P _{OUT} (W)	Gain (dB)	Eff (%)	P _{OUT} (W)	
Pulsed RF	1200	16	57	57	14	59	75	0.3
Pulsed RF	1300	16	56	55	14	58	75	0.3
Pulsed RF	1400	16	49	50	14	50	55	0.2

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	105	—	—	V
Drain Leakage Current	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1	μA
	$V_{DS} = 105\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	10	μA
On-State Resistance	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.4	—	Ω
Operating Gate Voltage	$V_{DS} = 50\text{ V}$, $I_{DQ} = 50\text{ mA}$	V_{GS}	3.0	3.5	4.0	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	—	1	μA

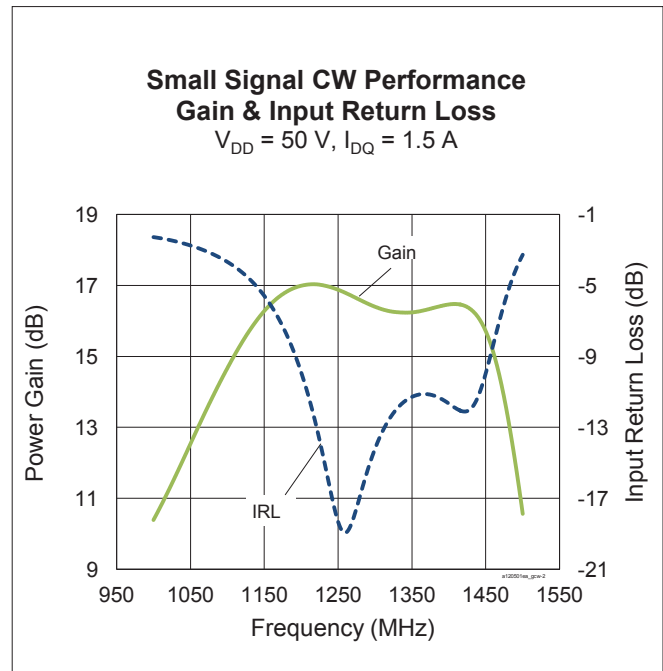
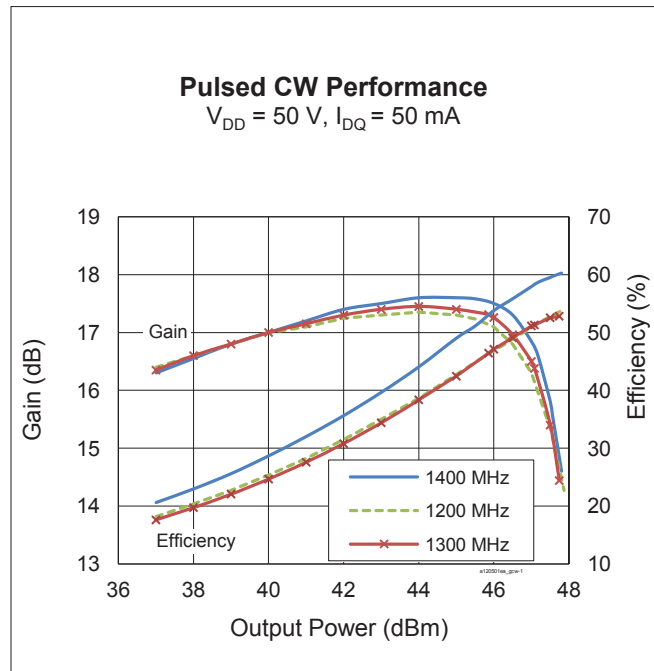
Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	105	V
Gate-Source Voltage	V_{GS}	-6 to +12	V
Junction Temperature	T_J	200	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C
Thermal Resistance ($T_{CASE} = 70^{\circ}\text{C}$, 50 W CW)	$R_{\theta JC}$	1.37	°C/W

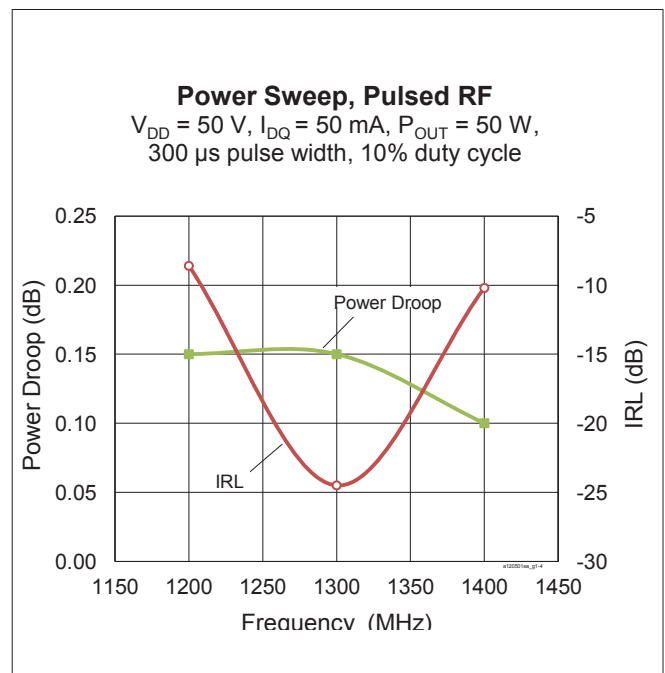
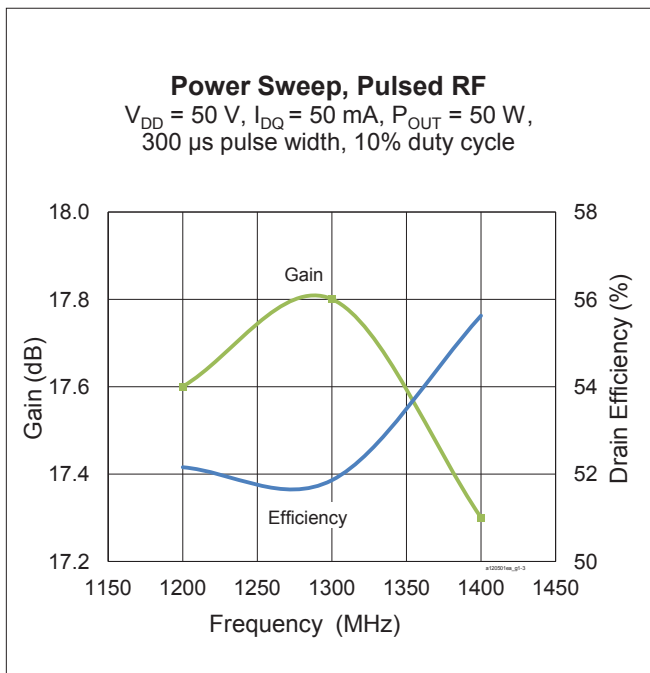
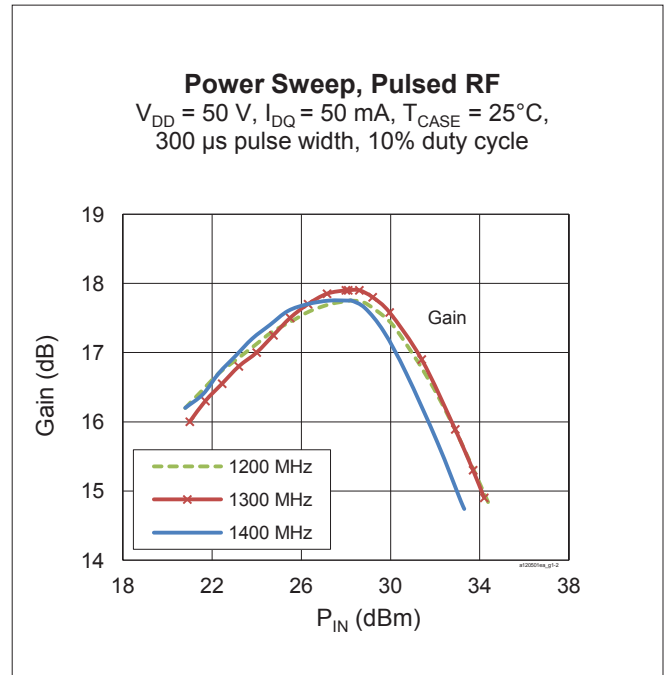
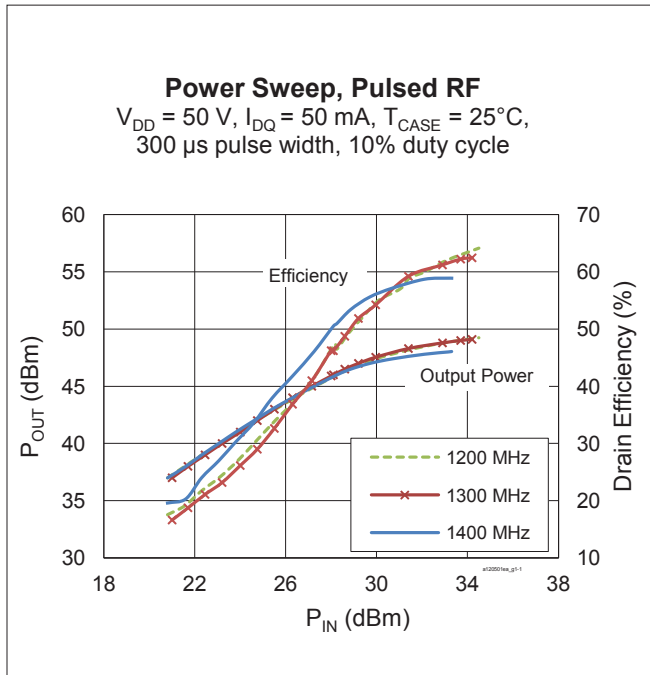
Ordering Information

Type and Version	Order Code	Package Description	Shipping
PTVA120501EA V1	PTVA120501EAV1XWSA1	H-36265-2, bolt-down	Tray
PTVA120501EA V1 R250	PTVA120501EAV1R250XTMA1	H-36265-2, bolt-down	Tape & Reel, 250 pcs

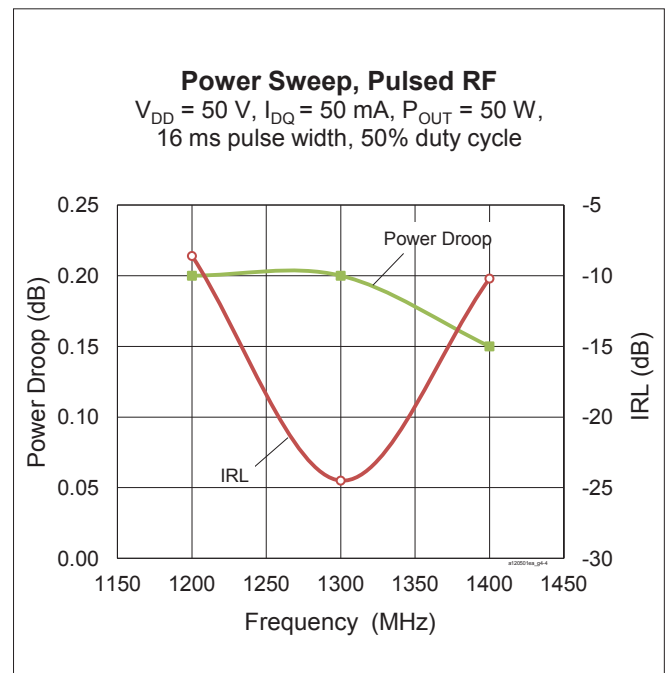
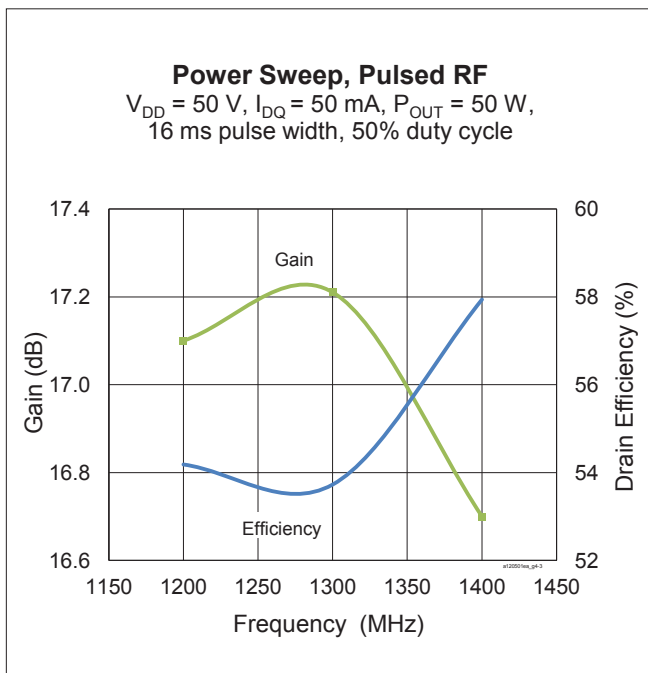
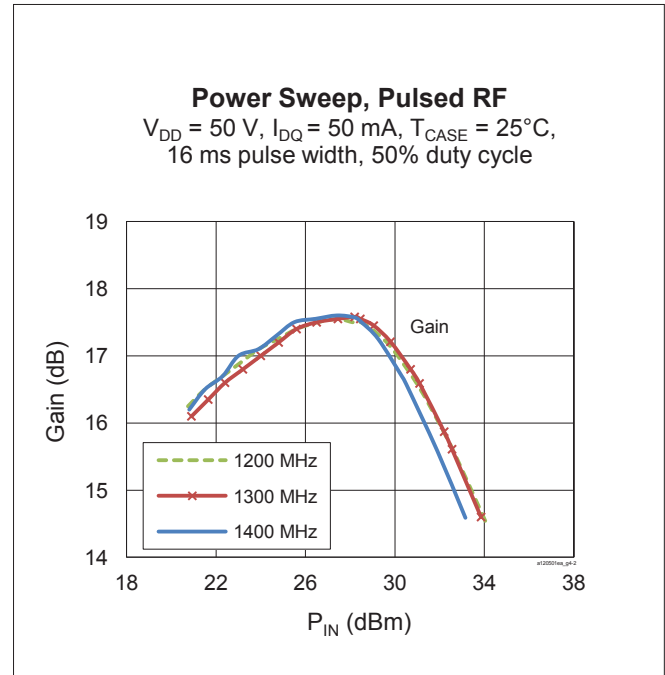
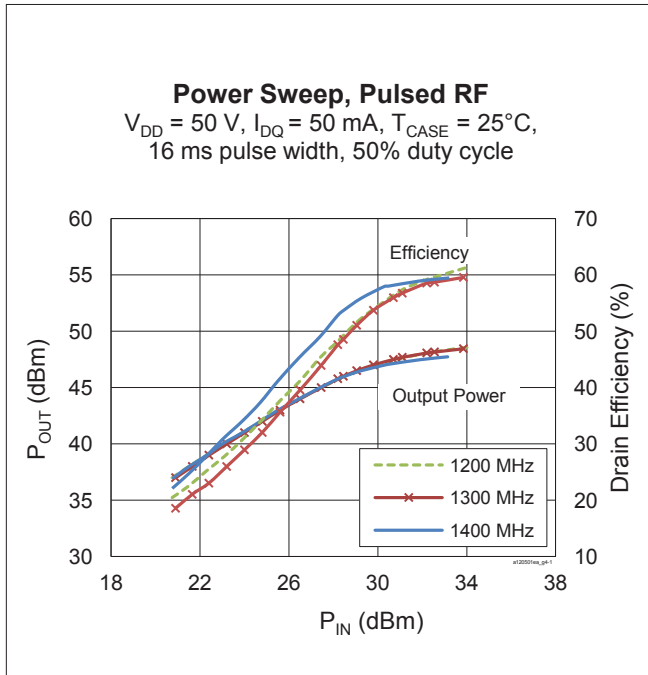
Typical Performance (data taken in a production test fixture)



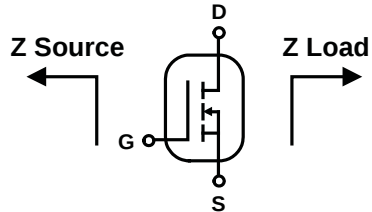
Typical Performance (cont.)



Typical Performance (cont.)



Broadband Circuit Impedance



Freq [MHz]	Z Source Ω		Z Load Ω	
	R	jX	R	jX
1200	8.07	-2.13	3.66	4.97
1300	5.13	-0.95	3.90	4.56
1400	5.64	2.24	3.25	5.36

Load Pull Performance

Load Pull at Max P_{OUT} Point – 16 μ s pulse width, 10% duty cycle, class AB, $V_{DD} = 50$ V, 50 mA

Freq [MHz]	ZI [Ω]	P _{IN} [dBm]	P _{OUT} [dBm]	P _{OUT} [W]	P _G [dB]	PAE Eff [%]	Z _{OUT} [Ω]
1200	3.04 – j2.16	30.68	47.30	53.70	16.62	45.56	3.19 – j1.55

Load Pull at Max G_T Point – 16 μ s pulse width, 10% duty cycle, class AB, $V_{DD} = 50$ V, 50 mA

Freq [MHz]	ZI [Ω]	P _{IN} [dBm]	P _{OUT} [dBm]	P _{OUT} [W]	P _G [dB]	PAE Eff [%]	Z _{OUT} [Ω]
1200	3.04 – j2.16	27.50	46.10	40.74	18.60	57.50	2.88 – j4.11

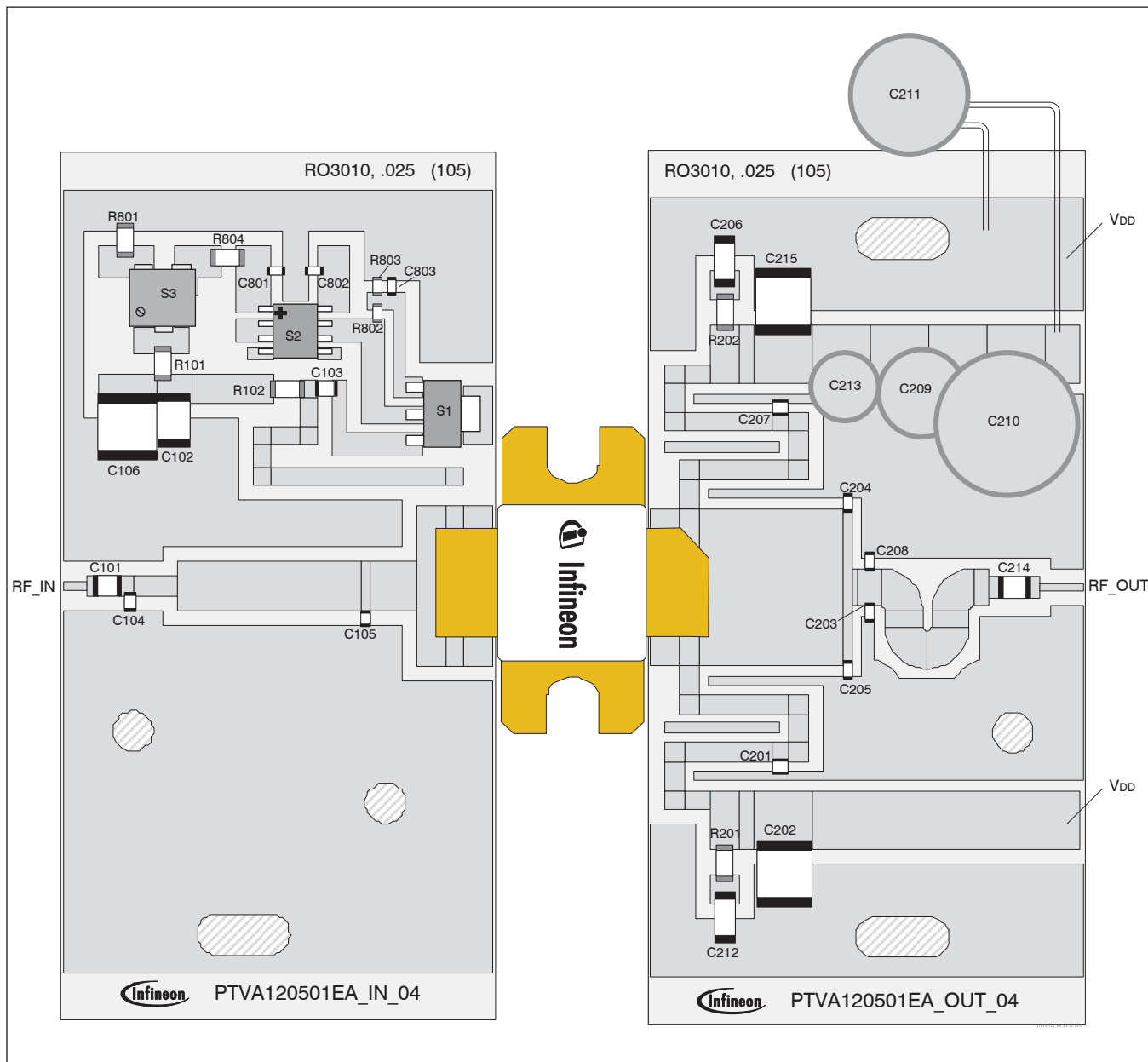
Load Pull at Max Efficiency Point – 16 μ s pulse width, 10% duty cycle, class AB, $V_{DD} = 50$ V, 50 mA

Freq [MHz]	ZI [Ω]	P _{IN} [dBm]	P _{OUT} [dBm]	P _{OUT} [W]	P _G [dB]	PAE Eff [%]	Z _{OUT} [Ω]
1200	3.04 – j2.16	27.55	46.15	41.21	18.60	57.20	2.88 – j4.06

Z Optimum – 16 μ s pulse width, 10% duty cycle, class AB, $V_{DD} = 50$ V, 50 mA

Freq [MHz]	ZI [Ω]	P _{IN} [dBm]	P _{OUT} [dBm]	P _{OUT} [W]	P _G [dB]	PAE Eff [%]	Z _{OUT} [Ω]
1200	3.04 – j2.16	28.70	46.57	45.39	17.87	50.46	2.92 – j3.12

Reference Circuit , 1200 – 1400 MHz



Reference Circuit (cont.)

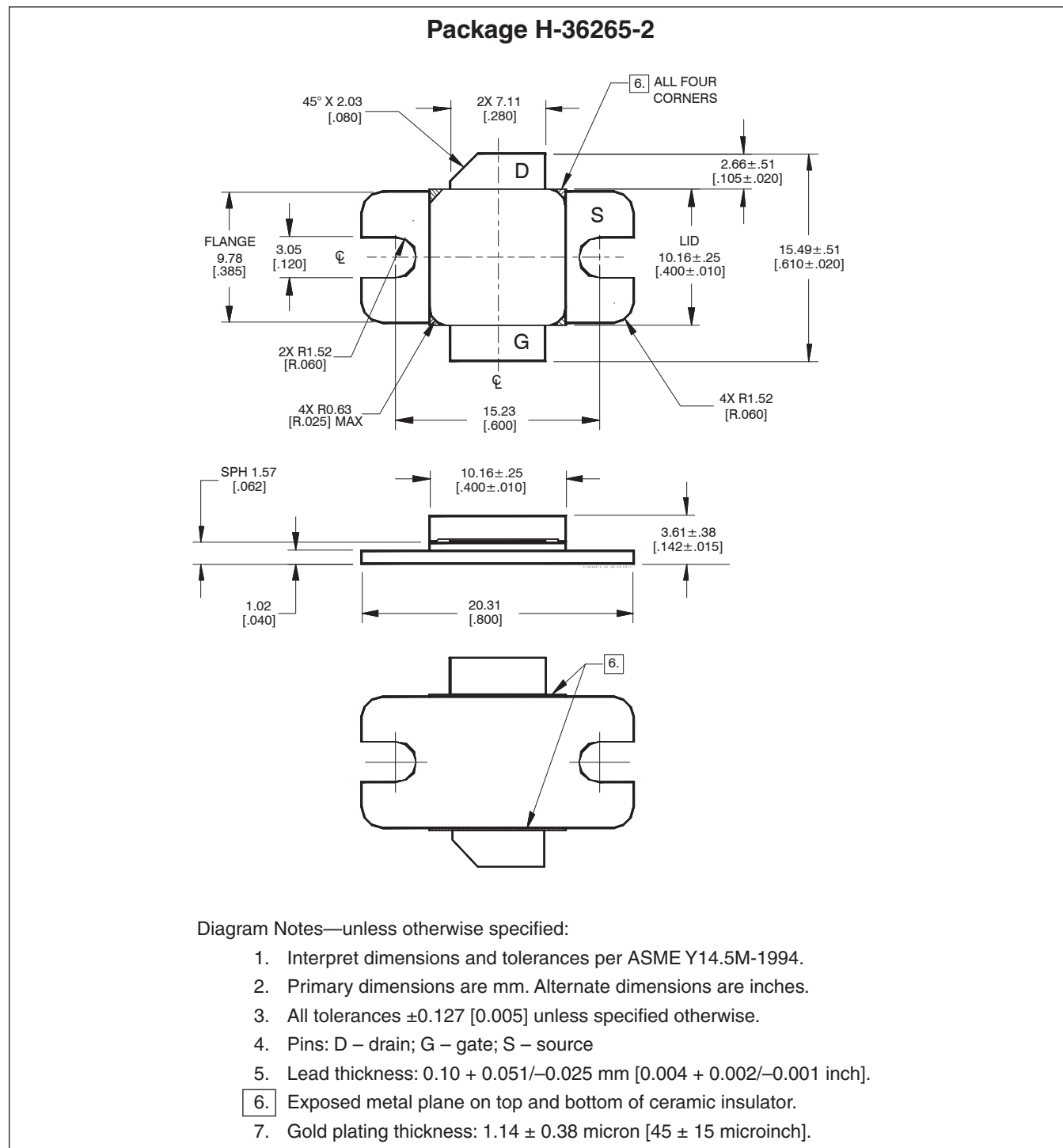
Reference Circuit Assembly

DUT	PTVA120501EA
Test Fixture Part No.	LTN/PTVA120501EA V1
PCB	Rogers 6006, 0.635 mm [0.025"] thick, 2 oz. copper, $\epsilon_r = 6.15$, $f = 1200 - 1400$ MHz

Components Information

Component	Description	Suggested Manufacturer	P/N
Input			
C101	Capacitor, 39 pF	ATC	ATC100B390KW500XB
C102	Capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C103	Capacitor, 33 pF	ATC	ATC100A330JW150XB
C104	Capacitor, 2.7 pF	ATC	ATC800A2R7BT
C105	Capacitor, 10 pF	ATC	ATC800A100JT
C106	Capacitor, 10 μ F	TDK Corporation	C5750X5R1H106K230KA
C801, C802, C803	Capacitor, 1000 pF	Panasonic Electronic Components	ECJ-1VB1H102K
R101	Resistor, 1000 Ω	Panasonic Electronic Components	ERJ-8GEYJ102V
R102	Resistor, 10 Ω	Panasonic Electronic Components	ERJ-8GEYJ100V
R801	Resistor, 2000 Ω	Panasonic Electronic Components	ERJ-8GEYJ202V
R802	Resistor, 1200 Ω	Panasonic Electronic Components	ERJ-3GEYJ122V
R803	Resistor, 1300 Ω	Panasonic Electronic Components	ERJ-3GEYJ132V
R804	Resistor, 100 Ω	Panasonic Electronic Components	ERJ-8GEYJ100V
S1	Transistor	Infineon Technologies	BCP56
S2	Voltage Regulator	Texas Instruments	LM78L05ACM
S3	Potentiometer, 2k Ω	Bourns Inc.	3224W-1-202E
Output			
C201, C207	Capacitor, 33 pF	ATC	ATC100A330JW150XB
C202, C215	Capacitor, 10 μ F	TDK Corporation	C5750X5R1H106K230KA
C203, C208	Capacitor, 3.9 pF	ATC	ATC800A3R9BT
C204, C205	Capacitor, 6.8 pF	ATC	ATC800A6R8BT
C206, C212	Capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C209	Capacitor, 22 μ F	Cornell Dubilier Electronics (CDE)	SEK220M100ST
C210	Capacitor, 100 μ F	Cornell Dubilier Electronics (CDE)	SK101M100ST
C211	Capacitor, 6800 μ F	Cornell Dubilier Electronics (CDE)	ECO-S2AP682EA
C213	Capacitor, 10 μ F	Cornell Dubilier Electronics (CDE)	SEK100M100ST
C214	Capacitor, 39 pF	ATC	ATC100B390KW500XB
R201, R202	Resistor, 5600 Ω	Panasonic Electronic Components	ERJ-8RQJ5R6V

Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page
<http://www.infineon.com/rfpower>

Revision History: 2013-09-24 Data Sheet

Previous Version: 2013-05-29 Advance Specification

Page	Subjects (major changes since last revision)
All	Data Sheet reflects released product specifications

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all?

Your feedback will help us to continuously improve the quality of this document.

Please send your proposal (including a reference to this document) to:

highpowerRF@infineon.com

To request other information, contact us at:

+1 877 465 3667 (1-877-GO-LDMOS) USA

or +1 408 776 0600 International



Edition 2013-09-24

Published by

Infineon Technologies AG

85579 Neubiberg, Germany

© 2013 Infineon Technologies AG

All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com/rfpower).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.